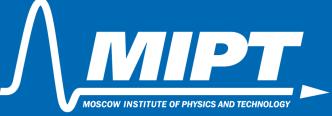


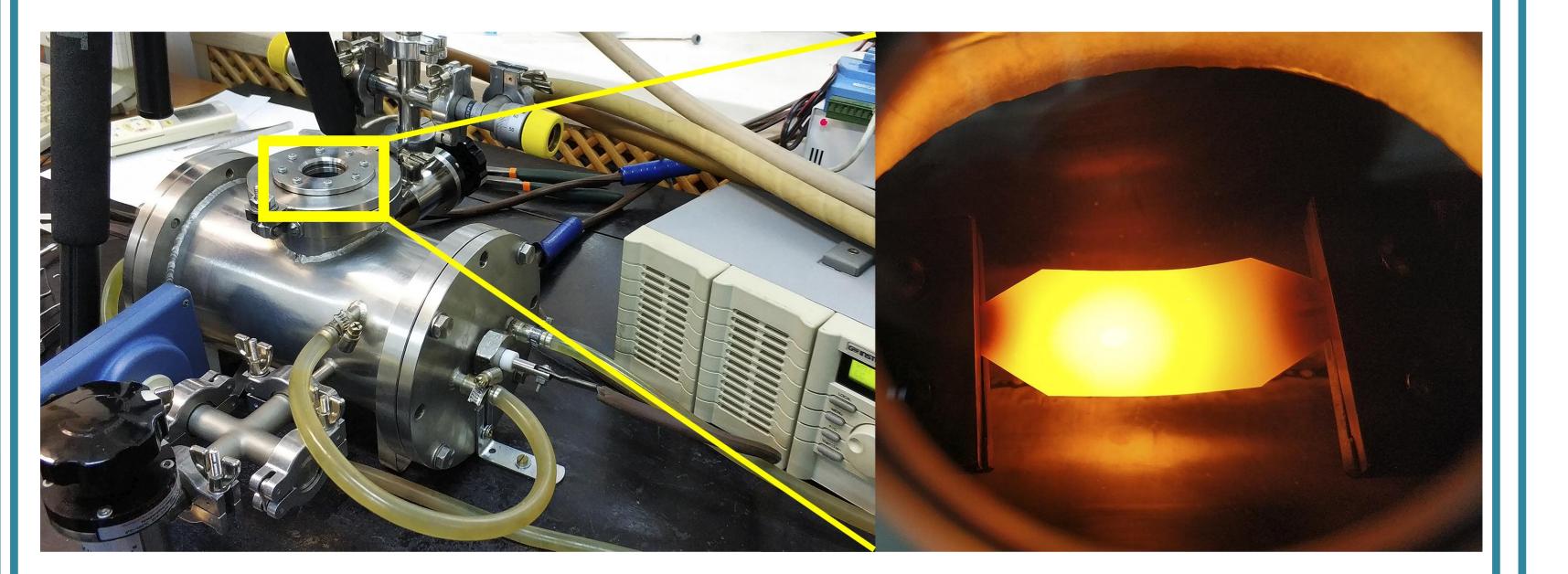
ULTRAFAST CVD GROWTH OF A MONOLAYER AND SINGLE-CRYSTAL GRAPHENE USING A COLD WALL REACTOR

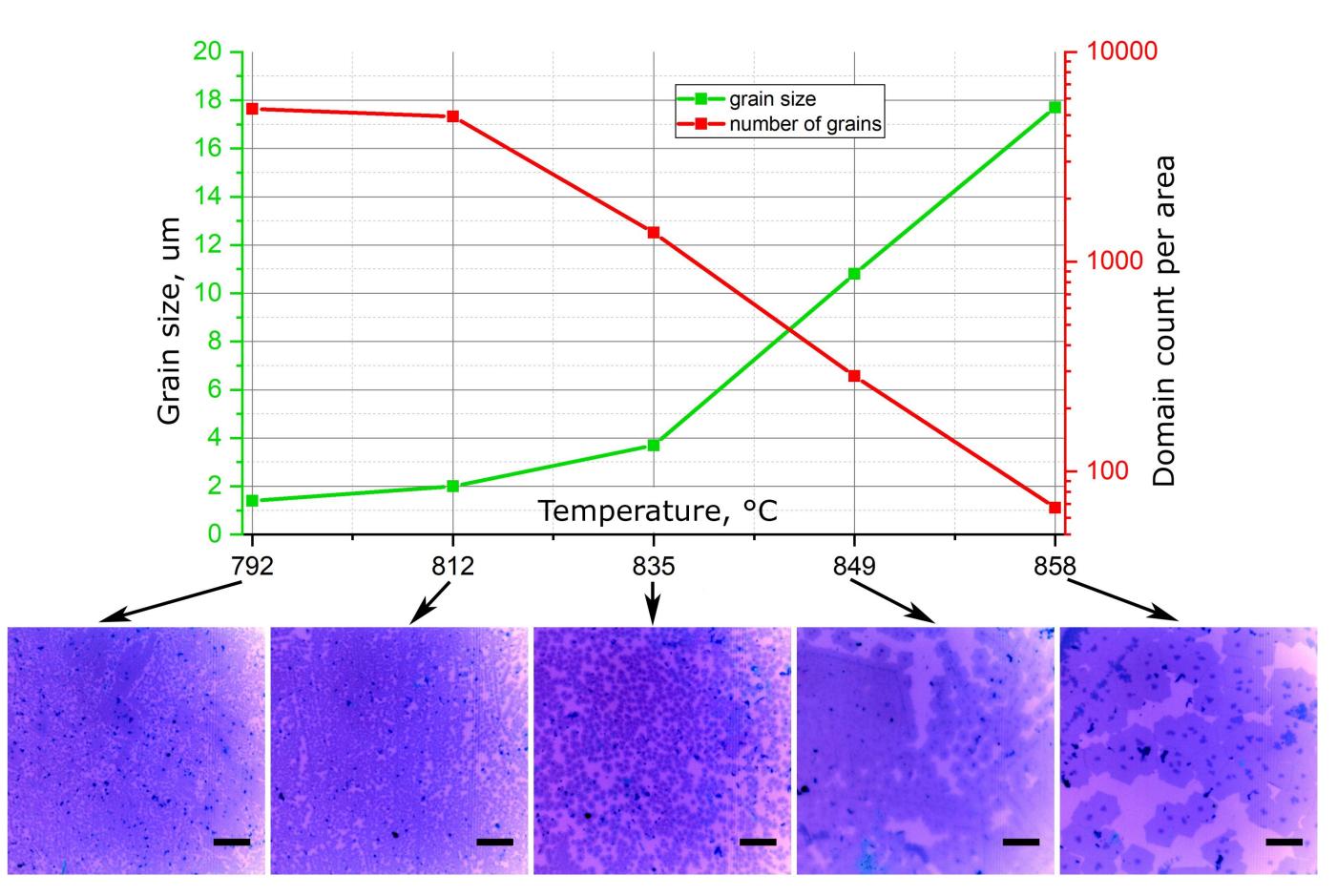


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COLD-WALL CVD SYNTHESIS OF GRAPHENE

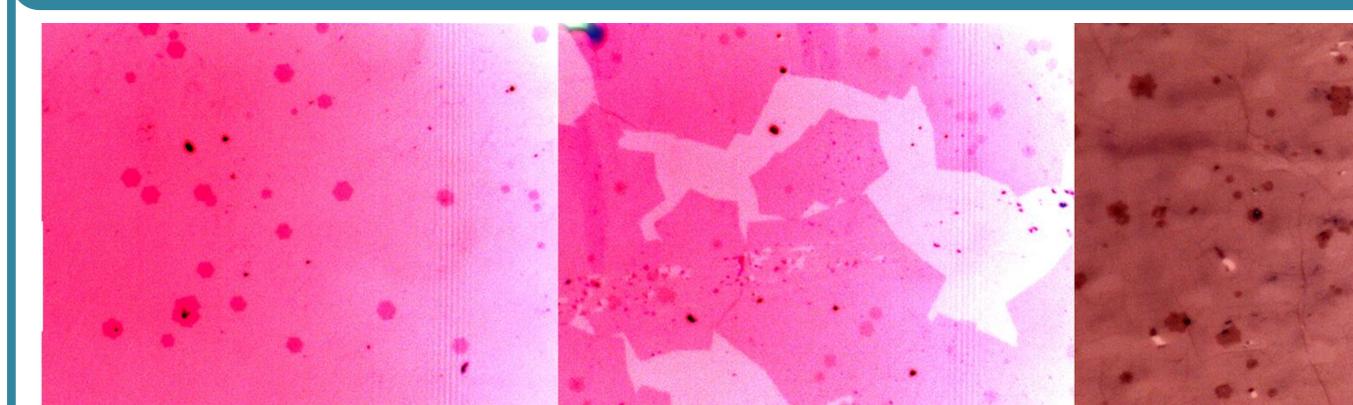
TEMPERATURE EFFECT





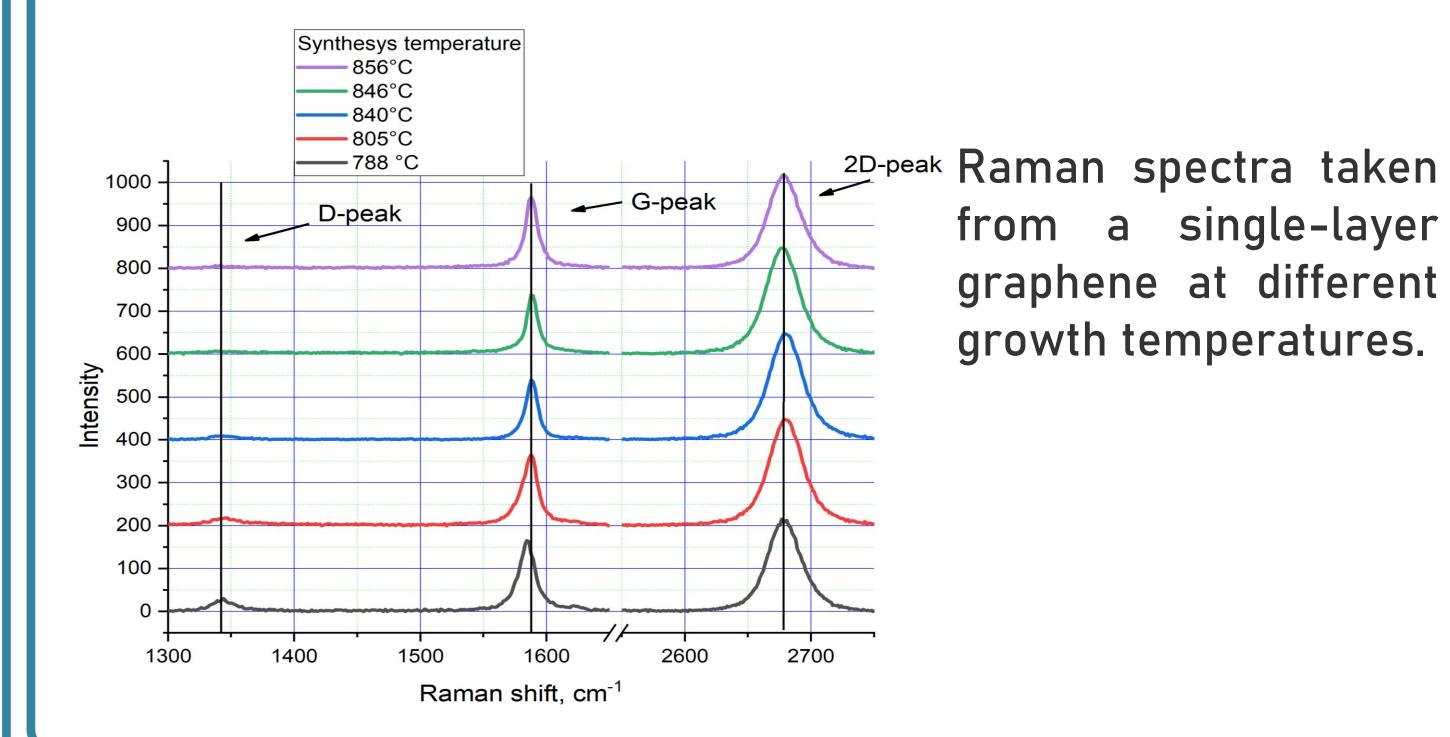
Cold wall CVD reactor (left) and a close-up of the experimental set-up during graphene growth on copper foil (right)

DURATION OF SYNTHESIS



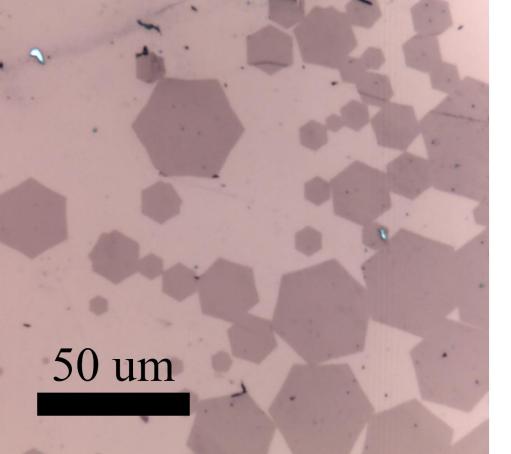
The size of graphene crystals and nucleation density as a function of growth temperature. Optical images of graphene crystals on Si/SiO2 substrate at different growth temperatures. All scale bars are 20um.

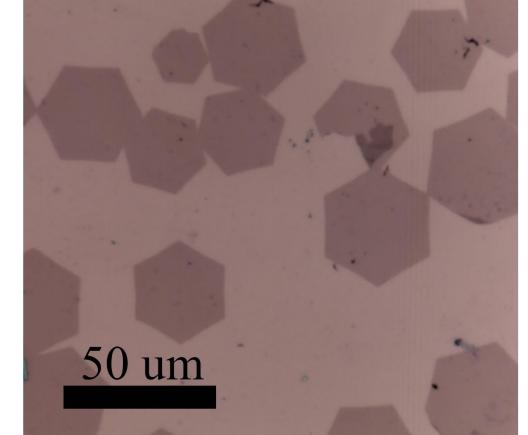
single-layer

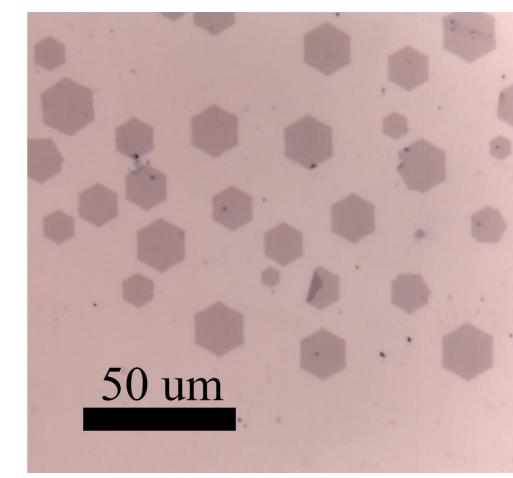


140 um

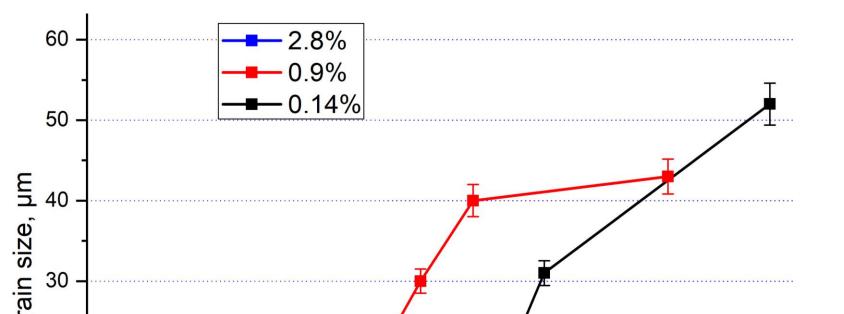
1 min 5 min 3 min Optical images of graphene monolayer growth at different stages from nucleation's (1 min) and growth (3 min) to form the monolayer (5 min)





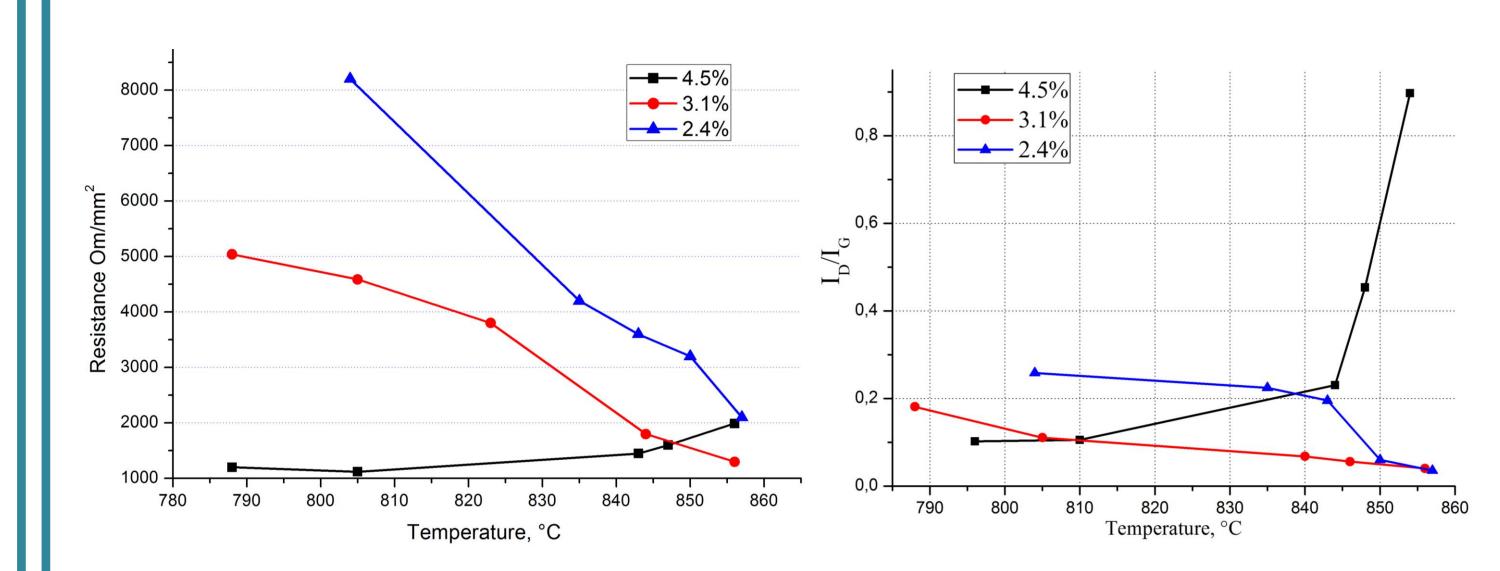


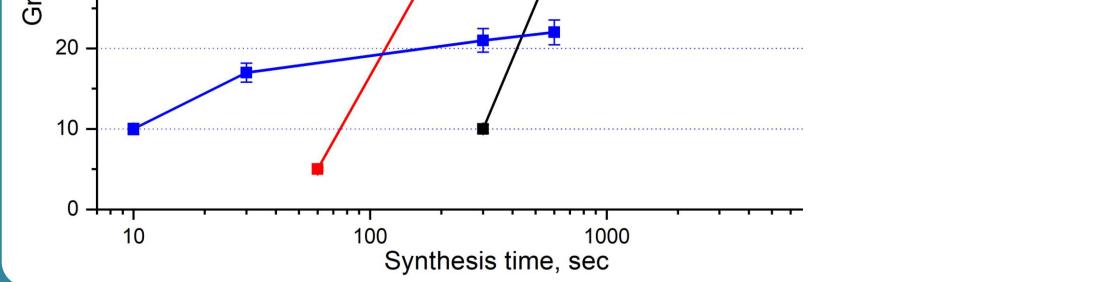
Optical images of an isolated graphene crystals transferred on Si/SiO2 substrate



The size of graphene crystals as a function of duration synthesis at different precursor (CH_4) concentrations.

PRECURSOR CONCENTRATION





CONCLUSIONS

Graphene monolayer can be grown at record time full cycle around 3-4 minutes using high temperature and precursor concentrations. To grow a high-quality graphene, a low precursor concentration (<0.3%) should be used. Exact control of the synthesis time allows growing isolated grains and monolayers of high-quality graphene.

The effect of different precursor concentrations on the sheet resistance (left) and Raman D/G intensity ratio at various temperatures

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